



SLOVENSKI STANDARD
oSIST prEN IEC 63378-6:2025
01-julij-2025

Standardizacija toplotnih lastnosti pri polprevodniških ohišjih - 6. del: Model toplotne upornosti in kapacitivnosti za napoved prehodne temperature na spojih in merilnih točkah

Thermal standardization on semiconductor packages - Part 6: Thermal resistance and capacitance model for transient temperature prediction at junction and measurement points

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Normalisation thermique des boîtiers de semiconducteurs - Partie 6: Modèle de résistance thermique et de capacité pour la prédiction de la température transitoire aux points de jonction et de mesure

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TITLE:

Thermal standardization on semiconductor packages - Part 6: Thermal resistance and capacitance model for transient temperature prediction at junction and measurement points

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